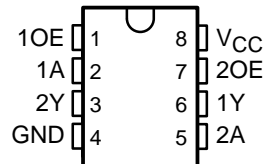


# SN74LVC2G126 DUAL BUS BUFFER GATE WITH 3-STATE OUTPUTS

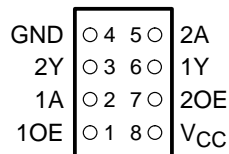
SCES205G – APRIL 1999 – REVISED MAY 2003

- Available in the Texas Instruments NanoStar™ and NanoFree™ Packages
- Supports 5-V  $V_{CC}$  Operation
- Inputs Accept Voltages to 5.5 V
- Max  $t_{pd}$  of 4 ns at 3.3 V
- Low Power Consumption, 10- $\mu$ A Max  $I_{CC}$
- $\pm 24$ -mA Output Drive at 3.3 V
- Typical  $V_{OLP}$  (Output Ground Bounce)  $< 0.8$  V at  $V_{CC} = 3.3$  V,  $T_A = 25^\circ\text{C}$
- Typical  $V_{OHV}$  (Output  $V_{OH}$  Undershoot)  $> 2$  V at  $V_{CC} = 3.3$  V,  $T_A = 25^\circ\text{C}$
- $I_{off}$  Supports Partial-Power-Down Mode Operation
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Protection Exceeds JESD 22
  - 2000-V Human-Body Model (A114-A)
  - 200-V Machine Model (A115-A)
  - 1000-V Charged-Device Model (C101)

DCT OR DCU PACKAGE  
(TOP VIEW)



YEA, YEP, YZA, OR YZP PACKAGE  
(BOTTOM VIEW)



## description/ordering information

This dual bus buffer gate is designed for 1.65-V to 5.5-V  $V_{CC}$  operation.

NanoStar™ and NanoFree™ package technology is a major breakthrough in IC packaging concepts, using the die as the package.

## ORDERING INFORMATION

$T_A$	PACKAGE†		ORDERABLE PART NUMBER	TOP-SIDE MARKING‡
–40°C to 85°C	NanoStar™ – WCSP (DSBGA) 0.17-mm Small Bump – YEA	Reel of 3000	SN74LVC2G126YEAR	— — — CN —
	NanoFree™ – WCSP (DSBGA) 0.17-mm Small Bump – YZA (Pb-free)		SN74LVC2G126YZAR	
	NanoStar™ – WCSP (DSBGA) 0.23-mm Large Bump – YEP		SN74LVC2G126YEPR	
	NanoFree™ – WCSP (DSBGA) 0.23-mm Large Bump – YZP (Pb-free)		SN74LVC2G126YZPR	
	SSOP – DCT	Reel of 3000	SN74LVC2G126DCTR	C26_ — —
	VSSOP – DCU	Reel of 3000	SN74LVC2G126DCUR	C26_ —
		Reel of 250	SN74LVC2G126DCUT	

† Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at [www.ti.com/sc/package](http://www.ti.com/sc/package).

‡ DCT: The actual top-side marking has three additional characters that designate the year, month, and assembly/test site.

DCU: The actual top-side marking has one additional character that designates the assembly/test site.

YEA/YZA, YEP/YZP: The actual top-side marking has three preceding characters to denote year, month, and sequence code, and one following character to designate the assembly/test site.



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# SN74LVC2G126

## DUAL BUS BUFFER GATE WITH 3-STATE OUTPUTS

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### description/ordering information (continued)

The SN74LVC2G126 is a dual bus driver/line driver with 3-state outputs. The outputs are disabled when the associated output-enable (OE) input is low.

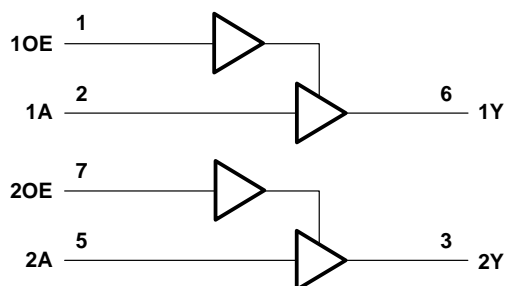
To ensure the high-impedance state during power up or power down, OE should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

This device is fully specified for partial-power-down applications using  $I_{off}$ . The  $I_{off}$  circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

FUNCTION TABLE  
(each buffer)

INPUTS		OUTPUT
OE	A	Y
H	H	H
H	L	L
L	X	Z

### logic diagram (positive logic)



**absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†**

Supply voltage range, $V_{CC}$	–0.5 V to 6.5 V
Input voltage range, $V_I$ (see Note 1)	–0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance or power-off state, $V_O$ (see Note 1)	–0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, $V_O$ (see Notes 1 and 2)	–0.5 V to $V_{CC} + 0.5$ V
Input clamp current, $I_{IK}$ ( $V_I < 0$ )	–50 mA
Output clamp current, $I_{OK}$ ( $V_O < 0$ )	–50 mA
Continuous output current, $I_O$	±50 mA
Continuous current through $V_{CC}$ or GND	±100 mA
Package thermal impedance, $\theta_{JA}$ (see Note 3): DCT package	220°C/W
DCU package	227°C/W
YEA/YZA package	140°C/W
YEP/YZP package	102°C/W
Storage temperature range, $T_{stg}$	–65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.  
2. The value of  $V_{CC}$  is provided in the recommended operating conditions table.  
3. The package thermal impedance is calculated in accordance with JESD 51-7.

**SN74LVC2G126**  
**DUAL BUS BUFFER GATE**  
**WITH 3-STATE OUTPUTS**  
 SCES205G – APRIL 1999 – REVISED MAY 2003

**recommended operating conditions (see Note 4)**

		MIN	MAX	UNIT
$V_{CC}$ Supply voltage	Operating	1.65	5.5	V
	Data retention only	1.5		
$V_{IH}$ High-level input voltage	$V_{CC} = 1.65\text{ V to }1.95\text{ V}$	$0.65 \times V_{CC}$		V
	$V_{CC} = 2.3\text{ V to }2.7\text{ V}$	1.7		
	$V_{CC} = 3\text{ V to }3.6\text{ V}$	2		
	$V_{CC} = 4.5\text{ V to }5.5\text{ V}$	$0.7 \times V_{CC}$		
$V_{IL}$ Low-level input voltage	$V_{CC} = 1.65\text{ V to }1.95\text{ V}$		$0.35 \times V_{CC}$	V
	$V_{CC} = 2.3\text{ V to }2.7\text{ V}$		0.7	
	$V_{CC} = 3\text{ V to }3.6\text{ V}$		0.8	
	$V_{CC} = 4.5\text{ V to }5.5\text{ V}$		$0.3 \times V_{CC}$	
$V_I$ Input voltage		0	5.5	V
$V_O$ Output voltage	High or low state	0	$V_{CC}$	V
	3-state	0	5.5	
$I_{OH}$ High-level output current	$V_{CC} = 1.65\text{ V}$		–4	mA
	$V_{CC} = 2.3\text{ V}$		–8	
	$V_{CC} = 3\text{ V}$		–16	
	$V_{CC} = 4.5\text{ V}$		–24	
$I_{OL}$ Low-level output current	$V_{CC} = 1.65\text{ V}$		4	mA
	$V_{CC} = 2.3\text{ V}$		8	
	$V_{CC} = 3\text{ V}$		16	
	$V_{CC} = 4.5\text{ V}$		24	
$\Delta t/\Delta v$ Input transition rise or fall rate	$V_{CC} = 1.8\text{ V} \pm 0.15\text{ V}, 2.5\text{ V} \pm 0.2\text{ V}$		20	ns/V
	$V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$		10	
	$V_{CC} = 5\text{ V} \pm 0.5\text{ V}$		5	
$T_A$ Operating free-air temperature		–40	85	°C

NOTE 4: All unused inputs of the device must be held at  $V_{CC}$  or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

**SN74LVC2G126**  
**DUAL BUS BUFFER GATE**  
**WITH 3-STATE OUTPUTS**

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**electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)**

PARAMETER		TEST CONDITIONS	V <sub>CC</sub>	MIN	TYP†	MAX	UNIT
V <sub>OH</sub>		I <sub>OH</sub> = –100 µA	1.65 V to 5.5 V	V <sub>CC</sub> –0.1			V
		I <sub>OH</sub> = –4 mA	1.65 V	1.2			
		I <sub>OH</sub> = –8 mA	2.3 V	1.9			
		I <sub>OH</sub> = –16 mA	3 V	2.4			
		I <sub>OH</sub> = –24 mA		2.3			
		I <sub>OH</sub> = –32 mA	4.5 V	3.8			
V <sub>OL</sub>		I <sub>OL</sub> = 100 µA	1.65 V to 5.5 V	0.1			V
		I <sub>OL</sub> = 4 mA	1.65 V	0.45			
		I <sub>OL</sub> = 8 mA	2.3 V	0.3			
		I <sub>OL</sub> = 16 mA	3 V	0.4			
		I <sub>OL</sub> = 24 mA		0.55			
		I <sub>OL</sub> = 32 mA	4.5 V	0.55			
I <sub>I</sub>	A or OE inputs	V <sub>I</sub> = 5.5 V or GND	0 to 5.5 V	±5			µA
I <sub>off</sub>		V <sub>I</sub> or V <sub>O</sub> = 5.5 V	0	±10			µA
I <sub>OZ</sub>		V <sub>O</sub> = 0 to 5.5 V	3.6 V	10			µA
I <sub>CC</sub>		V <sub>I</sub> = 5.5 V or GND, I <sub>O</sub> = 0	1.65 V to 5.5 V	10			µA
ΔI <sub>CC</sub>		One input at V <sub>CC</sub> – 0.6 V, Other inputs at V <sub>CC</sub> or GND	3 V to 5.5 V	500			µA
C <sub>i</sub>	Data inputs	V <sub>I</sub> = V <sub>CC</sub> or GND	3.3 V	3.5			pF
	Control inputs			4			
C <sub>o</sub>		V <sub>O</sub> = V <sub>CC</sub> or GND	3.3 V	6.5			pF

† All typical values are at V<sub>CC</sub> = 3.3 V, T<sub>A</sub> = 25°C.

**switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)**

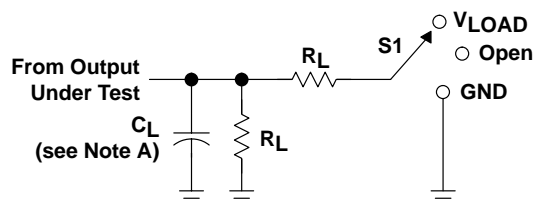
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V <sub>CC</sub> = 1.8 V ± 0.15 V		V <sub>CC</sub> = 2.5 V ± 0.2 V		V <sub>CC</sub> = 3.3 V ± 0.3 V		V <sub>CC</sub> = 5 V ± 0.5 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t <sub>pd</sub>	A	Y	3.5	9.8	1.7	4.9	1.4	4	1	3.2	ns
t <sub>en</sub>	OE	Y	3.5	10	1.7	5	1.5	4.1	1	3.1	ns
t <sub>dis</sub>	OE	Y	1.7	12.6	1	5.7	1	4.4	1	3.3	ns

**operating characteristics, T<sub>A</sub> = 25°**

PARAMETER			TEST CONDITIONS	V <sub>CC</sub> = 1.8 V	V <sub>CC</sub> = 2.5 V	V <sub>CC</sub> = 3.3 V	V <sub>CC</sub> = 5 V	UNIT
				TYP	TYP	TYP	TYP	
C <sub>pd</sub>	Power dissipation capacitance	Outputs enabled	f = 10 MHz	19	19	20	22	pF
		Outputs disabled		2	2	2	3	



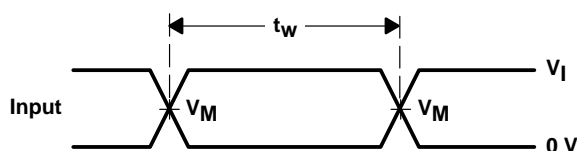
## PARAMETER MEASUREMENT INFORMATION



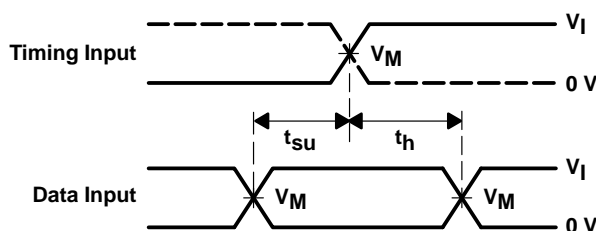
LOAD CIRCUIT

TEST	S1
$t_{PLH}/t_{PHL}$	Open
$t_{PLZ}/t_{PZL}$	$V_{LOAD}$
$t_{PHZ}/t_{PZH}$	GND

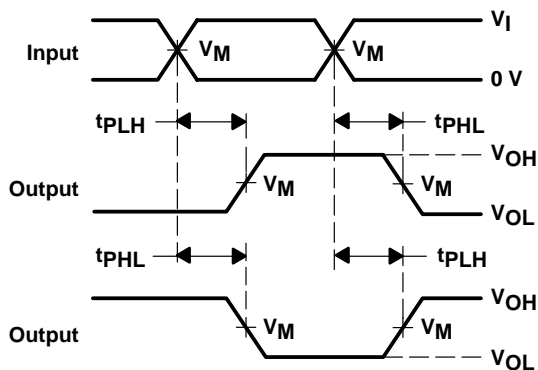
$V_{CC}$	INPUTS		$V_M$	$V_{LOAD}$	$C_L$	$R_L$	$V_{\Delta}$
	$V_I$	$t_r/t_f$					
$1.8\text{ V} \pm 0.15\text{ V}$	$V_{CC}$	$\leq 2\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	30 pF	1 k $\Omega$	0.15 V
$2.5\text{ V} \pm 0.2\text{ V}$	$V_{CC}$	$\leq 2\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	30 pF	500 $\Omega$	0.15 V
$3.3\text{ V} \pm 0.3\text{ V}$	3 V	$\leq 2.5\text{ ns}$	1.5 V	6 V	50 pF	500 $\Omega$	0.3 V
$5\text{ V} \pm 0.5\text{ V}$	$V_{CC}$	$\leq 2.5\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	50 pF	500 $\Omega$	0.3 V



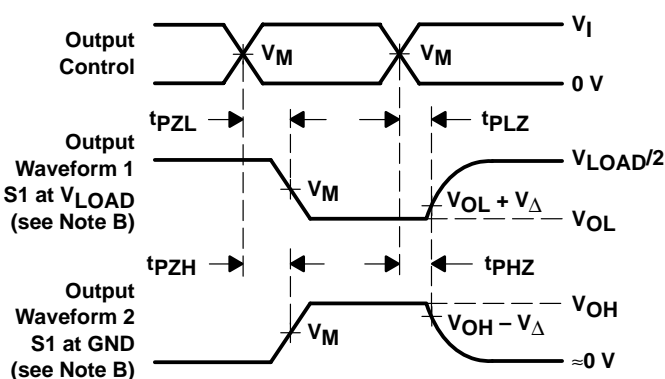
VOLTAGE WAVEFORMS  
PULSE DURATION



VOLTAGE WAVEFORMS  
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS  
PROPAGATION DELAY TIMES  
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS  
ENABLE AND DISABLE TIMES  
LOW- AND HIGH-LEVEL ENABLING

- NOTES:
- $C_L$  includes probe and jig capacitance.
  - Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
  - All input pulses are supplied by generators having the following characteristics:  $PRR \leq 10\text{ MHz}$ ,  $Z_O = 50\ \Omega$ .
  - The outputs are measured one at a time with one transition per measurement.
  - $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis}$ .
  - $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{en}$ .
  - $t_{PLH}$  and  $t_{PHL}$  are the same as  $t_{pd}$ .
  - All parameters and waveforms are not applicable to all devices.

Figure 1. Load Circuit and Voltage Waveforms

## DCT (R-PDSO-G8)

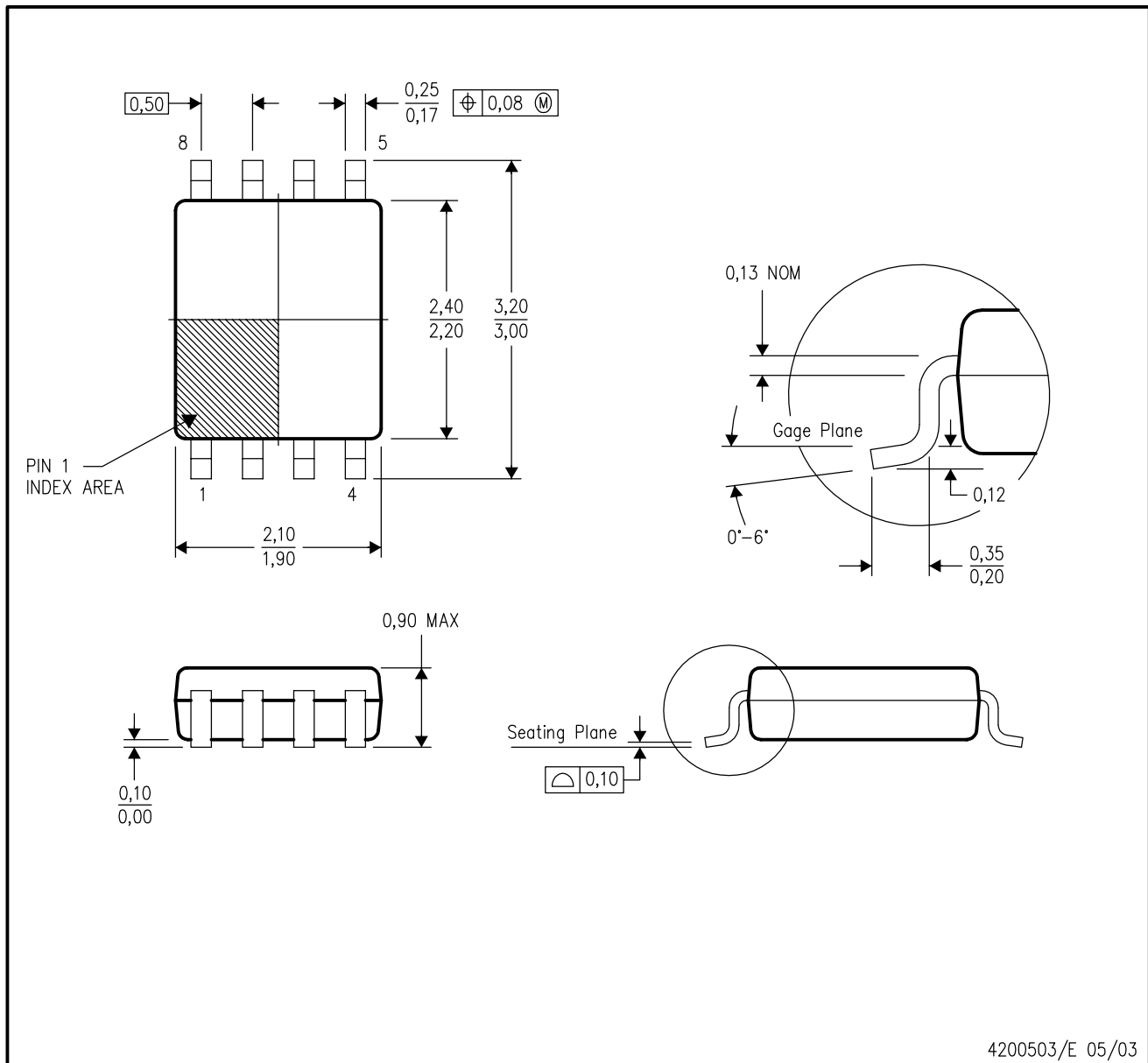
## PLASTIC SMALL-OUTLINE PACKAGE



- NOTES:
- All linear dimensions are in millimeters.
  - This drawing is subject to change without notice.
  - Body dimensions do not include mold flash or protrusion.
  - Falls within JEDEC MO-187 variation DA.

DCU (R-PDSO-G8)

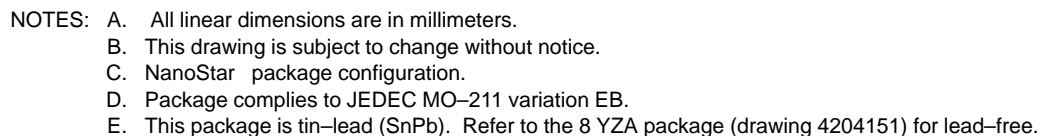
PLASTIC SMALL-OUTLINE PACKAGE (DIE DOWN)



- NOTES:
- All linear dimensions are in millimeters.
  - This drawing is subject to change without notice.
  - Body dimensions do not include mold flash or protrusion.
  - Falls within JEDEC MO-187 variation CA.

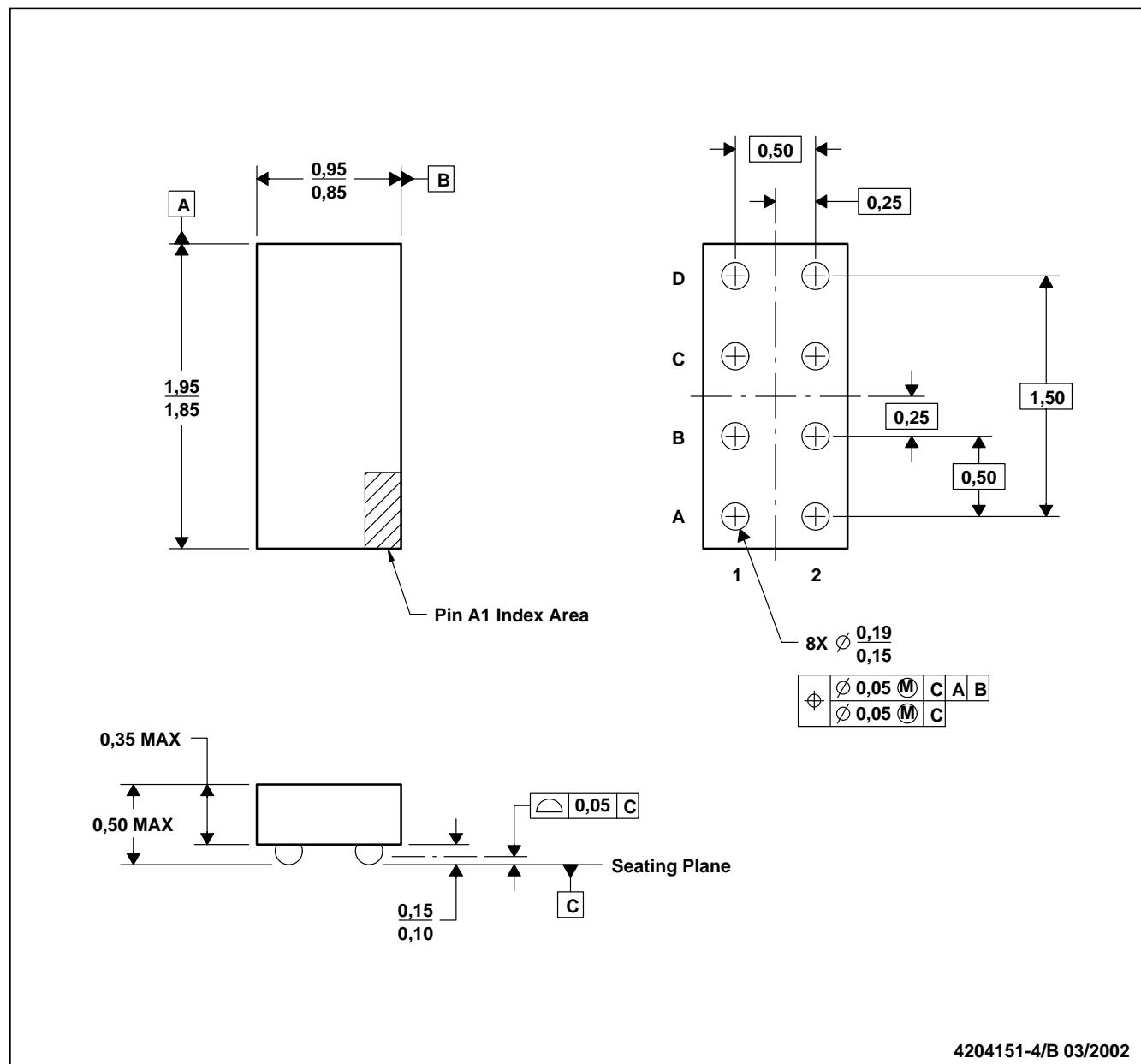


## DIE-SIZE BALL GRID ARRAY



## YZA (R-XBGA-N8)

## DIE-SIZE BALL GRID ARRAY



- NOTES:
- A. All linear dimensions are in millimeters.
  - B. This drawing is subject to change without notice.
  - C. NanoFree™ package configuration.
  - D. Package complies to JEDEC MO-211 variation EB.
  - E. This package is lead-free. Refer to the 8 YEA package (drawing 4203167) for tin-lead (SnPb).

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